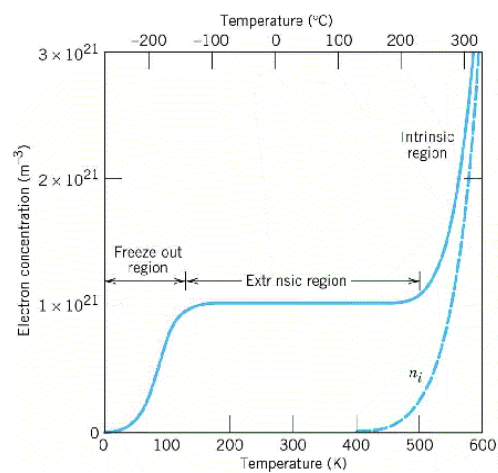


Chapter 18 Electrical properties

- The temperature variation of conductivity and carrier concentration
- Semiconductor devices

Temperature dependence of electric conductivity

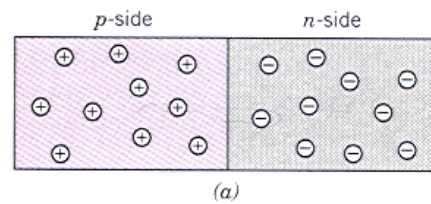


Intrinsic silicon and boron-doped silicon

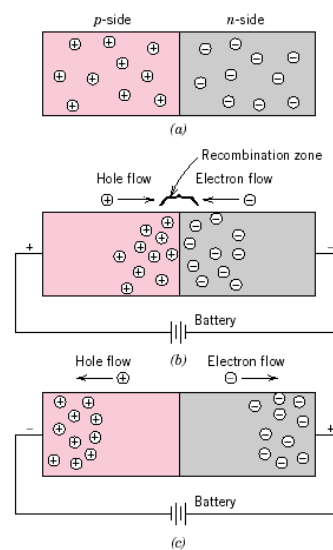
Semiconductor devices

□ Advantages of SC devices

□ A rectifier(diode):

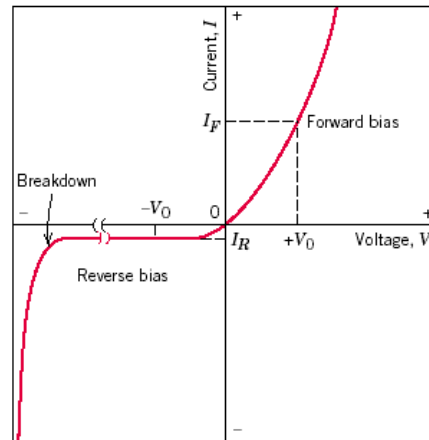


Semiconductor devices



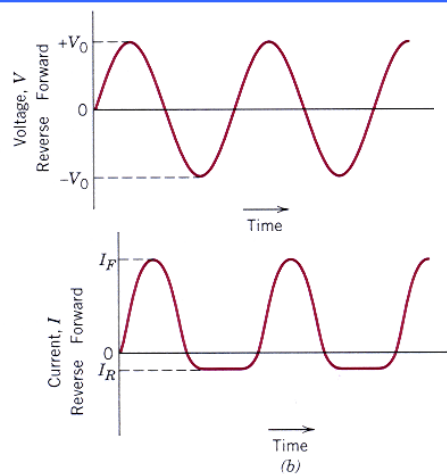
Semiconductor devices (*continue*)

- Current-voltage characteristics of a p-n junction for forward and reverse bias



The current-voltage characteristics of a p-n junction for forward and reverse biases

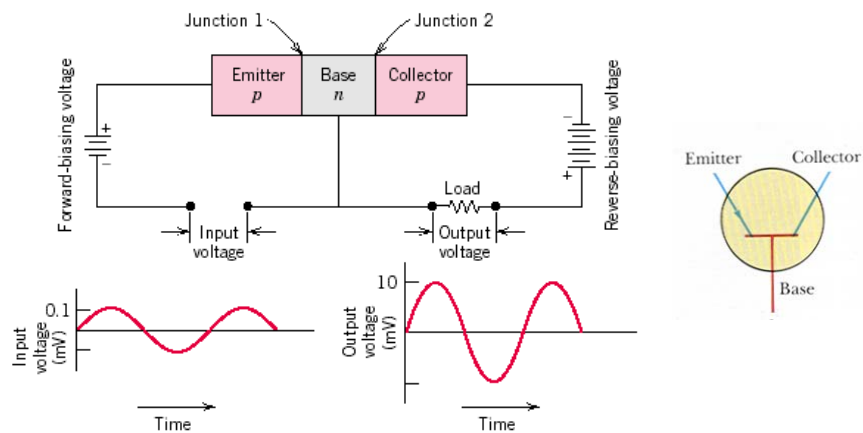
Semiconductor devices(*continue*)



Voltage versus time for the input to a p-n rectifying junction

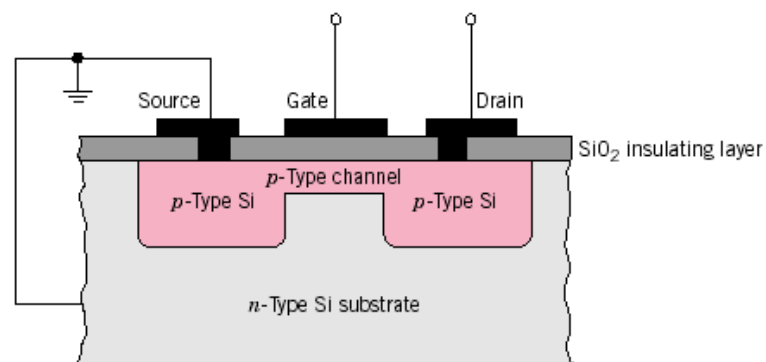
Semiconductor devices (*continue*)

□ p-n-p transistor



Semiconductor devices (*continue*)

□ Metal-oxide-semiconductor field-effect transistor(MOSFET)



Schematic cross-sectional view of MOSFET transistor

Summary
